

DDR4 SDRAM SODIMM

Addendum

MTA16ATF4G64HZ – 32GB

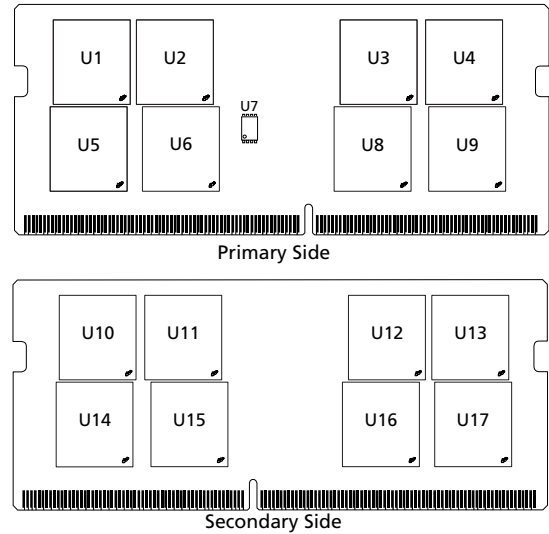
Introduction

Information provided here is in addition to or supersedes information provided in the Micron DDR4 SODIMM Core data sheet.

Features

- DDR4 functionality and operations supported as defined in the component data sheet
- Features and specifications supported in the Micron DDR4 SODIMM Core data sheet
- Fast data transfer rates: PC4-3200, PC4-2666
- 32GB (4 Gig x 64)
- Data bus inversion (DBI) for data bus
- Dual-rank
- 16 internal banks; 4 groups of 4 banks each

Figure 1: 260-Pin SODIMM



Options

- Operating temperature
 - Commercial ($0^{\circ}\text{C} \leq T_{\text{OPER}} \leq 95^{\circ}\text{C}$)
- Package
 - 260-pin DIMM (halogen-free)
- Frequency/CAS latency
 - 0.625ns @ CL = 22 (DDR4-3200)
 - 0.75ns @ CL = 19 (DDR4-2666)

Marking

- None
- Z
- 3G2
- 2G6

Table 1: Addressing

| Parameter | 32GB |
|-------------------------------|----------------------------|
| Row address | 128K A[16:0] |
| Column address | 1K A[9:0] |
| Device bank group address | 4 BG[1:0] |
| Device bank address per group | 4 BA[1:0] |
| Device configuration | 16Gb (2 Gig x 8), 16 banks |
| Module rank address | 2 CS_n[1:0] |



Table 2: Part Numbers and Timing Parameters – 32GB Modules

Base device: MT40A2G8, 16Gb DDR4 SDRAM

| Part Number ² | Module Density | Configuration | Module Bandwidth | Memory Clock/ Data Rate | Clock Cycles (CL _n RCD _n RP) |
|--------------------------|----------------|---------------|------------------|----------------------------|---|
| MTA16ATF4G64HZ-3G2__ | 32GB | 4 Gig x 64 | 25.6 GB/s | 0.625ns/3200 MT/s | 22-22-22 |
| MTA16ATF4G64HZ-2G6__ | 32GB | 4 Gig x 64 | 21.3 GB/s | 0.75ns/2666 MT/s | 19-19-19 |

- Notes:
1. The data sheet for the base device can be found on micron.com.
 2. All part numbers end with a two-place code (not shown) that designates component and PCB revisions. Consult factory for current revision codes. Example: MTA16ATF4G64HZ-3G2E1.

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DQ Map

Table 3: Component-to-Module DQ Map, R/C-E1

| Component Reference Number | Component DQ | Module DQ | Module Pin Number | Component Reference Number | Component DQ | Module DQ | Module Pin Number |
|----------------------------|--------------|-----------|-------------------|----------------------------|--------------|-----------|-------------------|
| U1 | 0 | 11 | 42 | U2 | 0 | 27 | 84 |
| | 1 | 8 | 28 | | 1 | 25 | 71 |
| | 2 | 10 | 41 | | 2 | 26 | 83 |
| | 3 | 9 | 29 | | 3 | 24 | 70 |
| | 4 | 14 | 38 | | 4 | 31 | 80 |
| | 5 | 12 | 24 | | 5 | 29 | 67 |
| | 6 | 15 | 37 | | 6 | 30 | 79 |
| | 7 | 13 | 25 | | 7 | 28 | 66 |
| U3 | 0 | 34 | 187 | U4 | 0 | 51 | 229 |
| | 1 | 33 | 173 | | 1 | 49 | 215 |
| | 2 | 35 | 186 | | 2 | 50 | 228 |
| | 3 | 32 | 174 | | 3 | 48 | 216 |
| | 4 | 39 | 182 | | 4 | 55 | 225 |
| | 5 | 36 | 170 | | 5 | 53 | 212 |
| | 6 | 38 | 183 | | 6 | 54 | 224 |
| | 7 | 37 | 169 | | 7 | 52 | 211 |
| U5 | 0 | 2 | 20 | U6 | 0 | 22 | 58 |
| | 1 | 0 | 8 | | 1 | 20 | 46 |
| | 2 | 3 | 21 | | 2 | 23 | 59 |
| | 3 | 1 | 7 | | 3 | 21 | 45 |
| | 4 | 6 | 16 | | 4 | 18 | 62 |
| | 5 | 4 | 4 | | 5 | 16 | 50 |
| | 6 | 7 | 17 | | 6 | 19 | 63 |
| | 7 | 5 | 3 | | 7 | 17 | 49 |
| U8 | 0 | 42 | 207 | U9 | 0 | 59 | 250 |
| | 1 | 40 | 195 | | 1 | 57 | 236 |
| | 2 | 43 | 208 | | 2 | 58 | 249 |
| | 3 | 41 | 194 | | 3 | 56 | 237 |
| | 4 | 46 | 203 | | 4 | 63 | 246 |
| | 5 | 45 | 190 | | 5 | 61 | 233 |
| | 6 | 47 | 204 | | 6 | 62 | 245 |
| | 7 | 44 | 191 | | 7 | 60 | 232 |

Table 3: Component-to-Module DQ Map, R/C-E1 (Continued)

| Component Reference Number | Component DQ | Module DQ | Module Pin Number | Component Reference Number | Component DQ | Module DQ | Module Pin Number |
|----------------------------|--------------|-----------|-------------------|----------------------------|--------------|-----------|-------------------|
| U10 | 0 | 49 | 215 | U11 | 0 | 33 | 173 |
| | 1 | 51 | 229 | | 1 | 34 | 187 |
| | 2 | 48 | 216 | | 2 | 32 | 174 |
| | 3 | 50 | 228 | | 3 | 35 | 186 |
| | 4 | 53 | 212 | | 4 | 36 | 170 |
| | 5 | 55 | 225 | | 5 | 39 | 182 |
| | 6 | 52 | 211 | | 6 | 37 | 169 |
| | 7 | 54 | 224 | | 7 | 38 | 183 |
| U12 | 0 | 25 | 71 | U13 | 0 | 8 | 28 |
| | 1 | 27 | 84 | | 1 | 11 | 42 |
| | 2 | 24 | 70 | | 2 | 9 | 29 |
| | 3 | 26 | 83 | | 3 | 10 | 41 |
| | 4 | 29 | 67 | | 4 | 12 | 24 |
| | 5 | 31 | 80 | | 5 | 14 | 38 |
| | 6 | 28 | 66 | | 6 | 13 | 25 |
| | 7 | 30 | 79 | | 7 | 15 | 37 |
| U14 | 0 | 57 | 236 | U15 | 0 | 40 | 195 |
| | 1 | 59 | 250 | | 1 | 42 | 207 |
| | 2 | 56 | 237 | | 2 | 41 | 194 |
| | 3 | 58 | 249 | | 3 | 43 | 208 |
| | 4 | 61 | 233 | | 4 | 45 | 190 |
| | 5 | 63 | 246 | | 5 | 46 | 203 |
| | 6 | 60 | 232 | | 6 | 44 | 191 |
| | 7 | 62 | 245 | | 7 | 47 | 204 |
| U16 | 0 | 20 | 46 | U17 | 0 | 0 | 8 |
| | 1 | 22 | 58 | | 1 | 2 | 20 |
| | 2 | 21 | 45 | | 2 | 1 | 7 |
| | 3 | 23 | 59 | | 3 | 3 | 21 |
| | 4 | 16 | 50 | | 4 | 4 | 4 |
| | 5 | 18 | 62 | | 5 | 6 | 16 |
| | 6 | 17 | 49 | | 6 | 5 | 3 |
| | 7 | 19 | 63 | | 7 | 7 | 17 |

I_{DD} Specifications

Table 4: DDR4 I_{DD} Specifications and Conditions (0° ≤ T_C ≤ 85°) – 32GB (Die Revision E)

Values are for the MT40A2G8 DDR4 SDRAM only and are computed from values specified in the 16Gb (2 Gig x 8) component data sheet

| Parameter | Symbol | 3200 | 2666 | Units |
|--|---|------|------|-------|
| One bank ACTIVATE-PRECHARGE current | I _{DD0} ¹ | 784 | 768 | mA |
| One bank ACTIVATE-PRECHARGE, wordline boost, I _{pp} current | I _{PP0} ¹ | 40 | 40 | mA |
| One bank ACTIVATE-READ-PRECHARGE current | I _{DD1} ¹ | 872 | 856 | mA |
| Precharge standby current | I _{DD2N} ² | 720 | 688 | mA |
| Precharge standby ODT current | I _{DD2NT} ¹ | 712 | 696 | mA |
| Precharge power-down current | I _{DD2P} ² | 608 | 608 | mA |
| Precharge quite standby current | I _{DD2Q} ² | 672 | 672 | mA |
| Active standby current | I _{DD3N} ² | 976 | 944 | mA |
| Active standby I _{pp} current | I _{PP3N} ² | 32 | 32 | mA |
| Active power-down current | I _{DD3P} ² | 800 | 768 | mA |
| Burst read current | I _{DD4R} ¹ | 1600 | 1472 | mA |
| Burst write current | I _{DD4W} ¹ | 1328 | 1240 | mA |
| Different logic rank burst refresh current (1x REF) | I _{DD5R} ¹ | 848 | 848 | mA |
| Different logic rank burst refresh I _{pp} current (1x REF) | I _{PP5R} ¹ | 48 | 48 | mA |
| Self refresh current: Normal temperature range (0°C to 85°C) | I _{DD6N (0-85°C)} ² | 848 | 848 | mA |
| Self refresh current: Extended temperature range (0°C to 95°C) | I _{DD6E (0-95°C)} ² | 1808 | 1808 | mA |
| Self refresh current: Reduced temperature range (0°C to 45°C) | I _{DD6R (0-45°C)} ² | 320 | 320 | mA |
| Auto self refresh current (25°C) | I _{DD6A (25°C)} ² | 176 | 176 | mA |
| Auto self refresh current (45°C) | I _{DD6A (45°C)} ² | 320 | 320 | mA |
| Auto self refresh current (75°C) | I _{DD6A (75°C)} ² | 816 | 816 | mA |
| Auto self refresh current (95°C) | I _{DD6A (95°C)} ² | 1808 | 1808 | mA |
| Auto self refresh I _{pp} current (0°C to 95°C) | I _{PP6X} ² | 96 | 96 | mA |
| Bank interleave read current | I _{DD7} ¹ | 1784 | 1752 | mA |
| Bank interleave read I _{pp} current | I _{PP7} ¹ | 128 | 128 | mA |
| Maximum power-down current | I _{DD8} ² | 576 | 576 | mA |

- Notes:
1. One module rank in the active I_{DD}/I_{pp}, the other rank in I_{DD2P}/I_{PP3N}.
 2. All ranks in this I_{DD}/I_{pp} condition.
 3. When T_C > 85°C, the I_{DD} and I_{pp} values must be derated. Refer to the base device data sheet I_{DD} and I_{pp} specification tables for derating values for the applicable die-revision.

Table 5: DDR4 I_{DD} Specifications and Conditions (0° ≤ T_C ≤ 85°) – 32GB (Die Revision B)

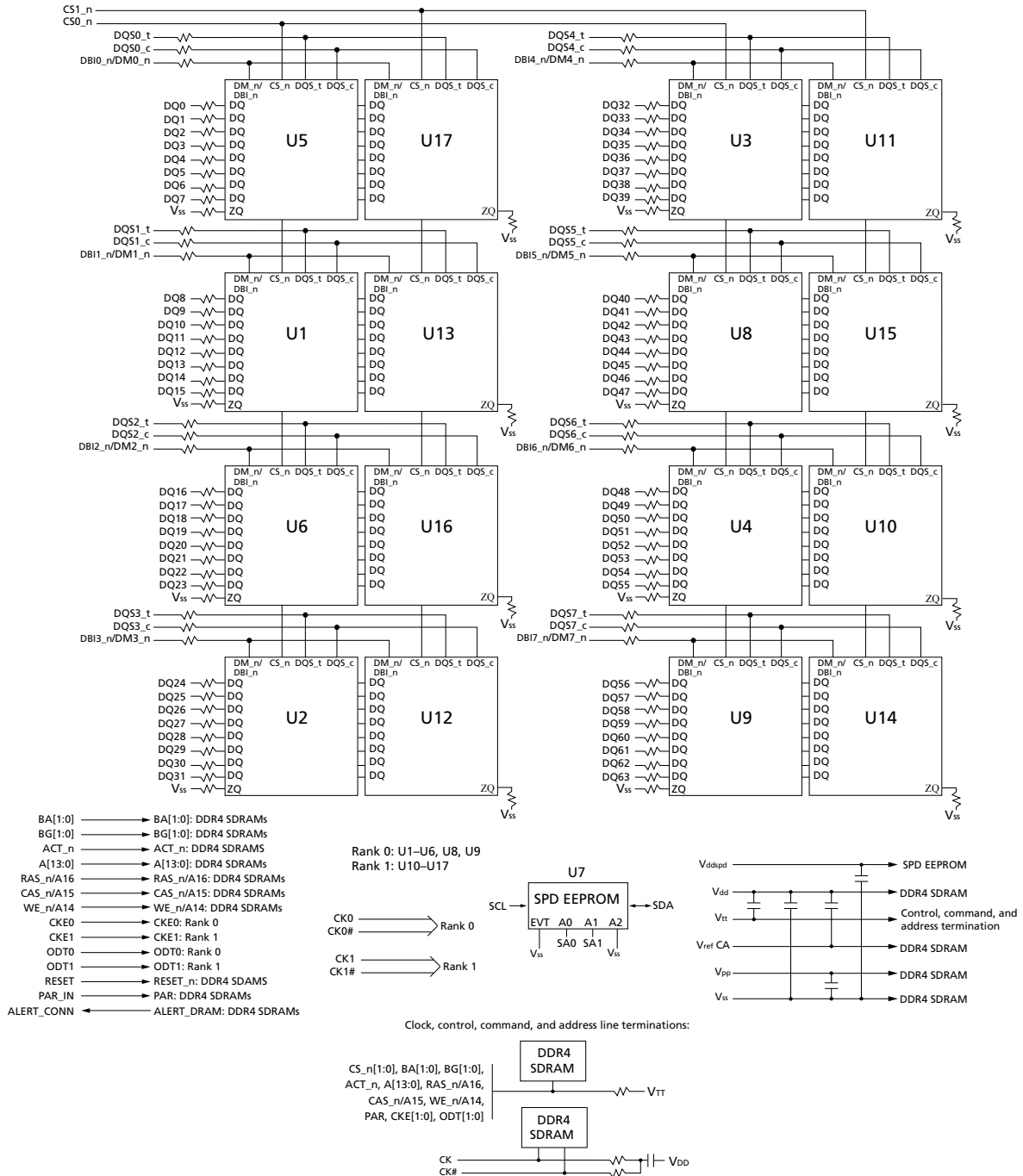
Values are for the MT40A2G8 DDR4 SDRAM only and are computed from values specified in the 16Gb (2 Gig x 8) component data sheet

| Parameter | Symbol | 3200 | 2666 | Units |
|--|---|------|------|-------|
| One bank ACTIVATE-PRECHARGE current | I _{DD0} ¹ | 848 | 832 | mA |
| One bank ACTIVATE-PRECHARGE, wordline boost, I _{PP} current | I _{PP0} ¹ | 56 | 56 | mA |
| One bank ACTIVATE-READ-PRECHARGE current | I _{DD1} ¹ | 936 | 920 | mA |
| Precharge standby current | I _{DD2N} ² | 832 | 800 | mA |
| Precharge standby ODT current | I _{DD2NT} ¹ | 792 | 776 | mA |
| Precharge power-down current | I _{DD2P} ² | 688 | 688 | mA |
| Precharge quite standby current | I _{DD2Q} ² | 752 | 752 | mA |
| Active standby current | I _{DD3N} ² | 1280 | 1248 | mA |
| Active standby I _{PP} current | I _{PP3N} ² | 48 | 48 | mA |
| Active power-down current | I _{DD3P} ² | 1104 | 1088 | mA |
| Burst read current | I _{DD4R} ¹ | 1960 | 1800 | mA |
| Burst write current | I _{DD4W} ¹ | 1808 | 1672 | mA |
| Different logic rank burst refresh current (1x REF) | I _{DD5R} ¹ | 976 | 960 | mA |
| Different logic rank burst refresh I _{PP} current (1x REF) | I _{PP5R} ¹ | 64 | 64 | mA |
| Self refresh current: Normal temperature range (0°C to 85°C) | I _{DD6N (0-85°C)} ² | 1072 | 1072 | mA |
| Self refresh current: Extended temperature range (0°C to 95°C) | I _{DD6E (0-95°C)} ² | 1936 | 1936 | mA |
| Self refresh current: Reduced temperature range (0°C to 45°C) | I _{DD6R (0-45°C)} ² | 464 | 464 | mA |
| Auto self refresh current (25°C) | I _{DD6A (25°C)} ² | 160 | 160 | mA |
| Auto self refresh current (45°C) | I _{DD6A (45°C)} ² | 464 | 464 | mA |
| Auto self refresh current (75°C) | I _{DD6A (75°C)} ² | 976 | 976 | mA |
| Auto self refresh current (95°C) | I _{DD6A (95°C)} ² | 1936 | 1936 | mA |
| Auto self refresh I _{PP} current (0°C to 95°C) | I _{PP6X} ² | 176 | 176 | mA |
| Bank interleave read current | I _{DD7} ¹ | 1912 | 1864 | mA |
| Bank interleave read I _{PP} current | I _{PP7} ¹ | 104 | 104 | mA |
| Maximum power-down current | I _{DD8} ² | 640 | 640 | mA |

- Notes:
1. One module rank in the active I_{DD}/I_{PP}, the other rank in I_{DD2P}/I_{PP3N}.
 2. All ranks in this I_{DD}/I_{PP} condition.
 3. When T_C > 85°C, the I_{DD} and I_{PP} values must be derated. Refer to the base device data sheet I_{DD} and I_{PP} specification tables for derating values for the applicable die-revision.

Functional Block Diagram

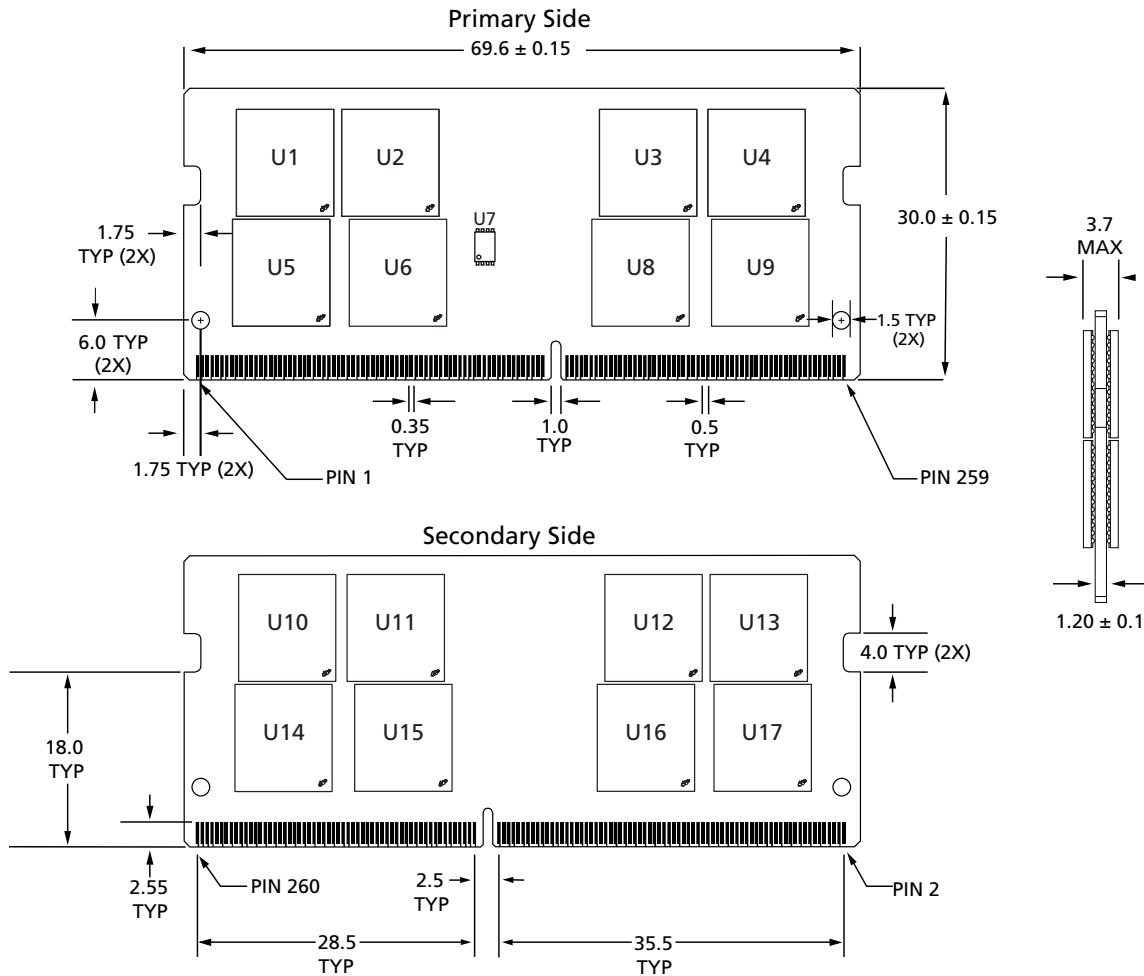
Figure 2: Functional Block Diagram, R/C-E1



Note: 1. The ZQ ball on each DDR4 component is connected to an external 240Ω ±1% resistor that is tied to ground. It is used for the calibration of the component's ODT and output driver.

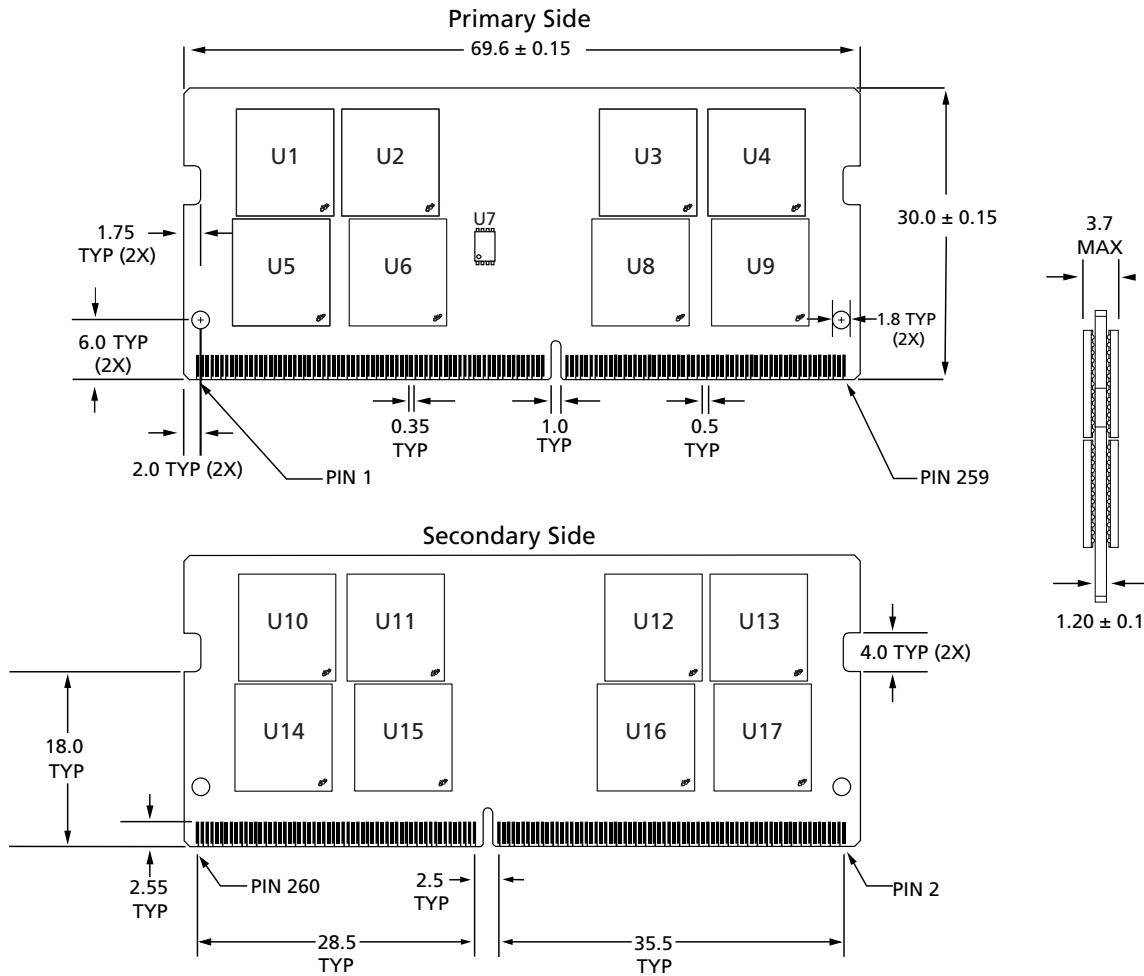
Module Dimensions

Figure 3: 260-Pin DDR4 SODIMM - PCB 2762, 2868 (R/C E1)



- Notes:
1. All dimensions are in millimeters; MAX/MIN or typical (TYP) where noted.
 2. The dimensional diagram is for reference only.
 3. Tooling hole dimensions on this PCB do not conform to the JEDEC MO-310 specification. All other dimensions conform to MO-310. Contact factory for further detail.

Figure 4: 260-Pin DDR4 SODIMM - PCB 3220 (R/C E1)



- Notes: 1. All dimensions are in millimeters; MAX/MIN or typical (TYP) where noted.
 2. The dimensional diagram is for reference only. Refer to JEDEC MO-310.

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